

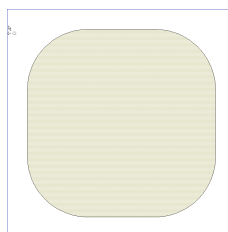
CS08H5P0MS2P

Bi-Directional ESD Diode

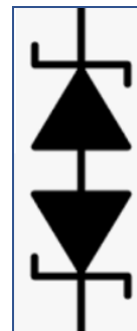
Wafer Information

Item	Description
Wafer Size	6 inch (150mm)
Wafer Thickness	150um ± 15um
Die Size (with scribe lane)	200um x 200um
Bond Pad Opening	140um x 140um
Scribe Lane Width	40um
Gross Die Per Wafer	382000
Top Metal (for wire bond)	4um AlSiCu
Backside Metal (for die bond)	TiNiAgSn 1/3/5/14KA

Die Appearance



Circuit Diagram



- Complies with IEC 61000-4-2 standards:
Contact discharge: ±16kV

Absolute Maximum Ratings (T_A=25 °C unless otherwise specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (8/20μs)	Ppk	60	W
Peak Pulse Current (8/20μs)	IPP	5	A
Operating Temperature Range	T _J	-55 to +125	°C
Storage Temperature Range	T _{stg}	-55 to +150	°C

Electrical Characteristics (T_A=25 °C unless otherwise specified)

Parameter	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	5.6		7.6	V	IT = 1mA
Reverse Leakage Current	IR			1	uA	VRWM = 5V
Clamping Voltage	VC			9	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	VC			12	V	IPP = 5A (8 x 20μs pulse)
Junction Capacitance	C _J		10		pF	VR = 0V, f = 1MHz

Note: Electrical parameters are only for die, performance may alter after assembly.